AMENDED CLAIM SET

1. - 7. (canceled)

8. (currently amended) A semiconductor field effect device having a gate dielectric and a gate, wherein said gate comprises ~~a compound comprising Ta and N~~ TaSiN disposed over said gate dielectric, wherein said ~~compound~~ TaSiN has ~~a resistivity below about 20mΩcm, and wherein in said compound~~ the elemental ratio of N to Ta greater than about 0.9:1, and a workfunction between about 4.31eV and 4.4eV.

9. - 11. (canceled)

12. (currently amended) The field effect device of claim ~~9~~ 8, wherein in said TaSiN the Si to Ta elemental ratio is between about ~~0.35 and 0.5~~ 0.35:1 and 0.5:1.

13. (currently amended) The field effect device of claim 12, wherein said TaSiN has ~~an~~ a substantially amorphous material structure.

14. (canceled)

15. (original) The field effect device of claim 8, wherein said gate dielectric has an

equivalent oxide thickness of less than about 5nm.

16. (original) The field effect device of claim 15, wherein said gate dielectric has an equivalent oxide thickness of less than about 2nm.

17. (original) The field effect device of claim 8, wherein said gate dielectric comprises SiO_2.

18. (original) The field effect device of claim 8, wherein said gate dielectric comprises a high-k dielectric material.

19. (original) The field effect device of claim 8, wherein said device is a Si based MOS transistor.

20. (original) The field effect device of claim 19, wherein said device is an NMOS transistor.

21. (currently amended) The field effect device of claim 20, wherein said NMOS transistor has a threshold voltage between about ~~0.15V and 0.55V~~ 0.36V and 0.45V.

22. - 32. (canceled)

33. (currently amended) A processor, comprising:

at least one chip, wherein said chip comprises at least one semiconductor field effect device having a gate dielectric and a gate, wherein said gate comprises ~~a compound comprising Ta and N~~ TaSiN disposed over said gate dielectric, wherein said ~~compound~~ TaSiN has ~~a resistivity below about 20mΩcm, and wherein in said compound~~ the elemental ratio of N to Ta greater than about 0.9:1, and a workfunction between about 4.31eV and 4.4eV.

34. (original) The processor of claim 33, wherein said processor is a digital processor.

35. (original) The processor of claim 33, wherein said processor comprises at least one analog circuit.

36. (new) The field effect device of claim , wherein TaSiN has a resistivity below about 20mΩcm.